

Abstract

Radiation-emitting semiconductor component and method for producing it

The invention relates to a radiation-emitting semiconductor component having a radiation-transmissive substrate (1), on the underside of which a radiation-generating layer (2) is arranged, in which the substrate (1) has inclined side areas (3), in which the refractive index of the substrate (1) is greater than the refractive index of the radiation-generating layer, in which the difference in refractive index results in an unilluminated substrate region (4), into which no photons are coupled directly from the radiation-generating layer, and in which the substrate (1) has essentially perpendicular side areas (5) in the unilluminated region. The component has the advantage that it can be produced with a better area yield from a wafer.

Figure 1